Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

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December 2014

FGH12040WD

1200 V, 40 A Field Stop Trench IGBT

Features

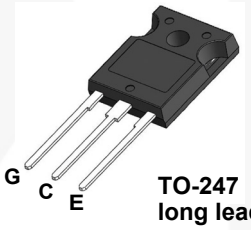
- Maximum Junction Temperature : T_J = 175°C
- Positive Temperature Co-efficient for Easy Parallel Operating
- Low Saturation Voltage: $V_{CE(sat)}$ = 2.3 V (Typ.) @ I_C = 40 A
- 100% of The Parts Tested for I_{LM} (1)
- Short Circuit Ruggedness > 5 us @ 150°C
- High Input Impedance
- RoHS Compliant

General Description

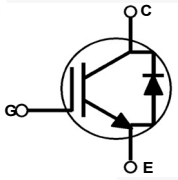
Using novel field stop IGBT technology, Fairchild's new series of field stop 2nd generation IGBTs offer the optimum performance for welder applications where low conduction and switching losses are essential.

Applications

- Only for Welder



TO-247
long leads



Absolute Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Description		FGH12040WD_F155	Unit
V_{CES}	Collector to Emitter Voltage		1200	V
V_{GES}	Gate to Emitter Voltage		±25	V
	Transient Gate to Emitter Voltage		±30	V
I_C	Collector Current	@ T_C = 25°C	80	A
	Collector Current	@ T_C = 100°C	40	A
I_{LM} (1)	Clamped Inductive Load Current	@ T_C = 25°C	100	A
I_{CM} (2)	Pulsed Collector Current		100	A
I_F	Diode Continuous Forward Current	@ T_C = 25°C	80	A
	Diode Continuous Forward Current	@ T_C = 100°C	40	A
I_{FM} (2)	Diode Maximum Forward Current		100	A
SCWT (3)	Short Circuit Withstand Time,	@ T_C = 150°C	5	us
P_D	Maximum Power Dissipation	@ T_C = 25°C	428	W
	Maximum Power Dissipation	@ T_C = 100°C	214	W
T_J	Operating Junction Temperature		-55 to +175	°C
T_{stg}	Storage Temperature Range		-55 to +175	°C
T_L	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds		300	°C

Notes:
1. V_{CC} = 600 V, V_{GE} = 15 V, I_C = 100 A, R_G = 23 Ω , Inductive Load
2. Repetitive rating : Pulse width limited by max. junction temperature
3. V_{CC} = 600 V, V_{GE} = 12 V

Thermal Characteristics

Symbol	Parameter	FGH12040WD_F155	Unit
$R_{\theta JC}$(IGBT)	Thermal Resistance, Junction to Case	0.35	°C/W
$R_{\theta JC}$(Diode)	Thermal Resistance, Junction to Case	1.4	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	40	°C/W

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FGH12040WD_F155	FGH12040WD	TO-247 G03	Tube	-	-	30

Electrical Characteristics of the IGBT T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
BV_{CES}	Collector to Emitter Breakdown Voltage	V_{GE} = 0 V, I_C = 250 uA	1200	-	-	V
ΔBV_{CES} / ΔT_J	Temperature Coefficient of Breakdown Voltage	V_{GE} = 0 V, I_C = 250 uA	-	1.2	-	V/°C
I_{CES}	Collector Cut-Off Current	V_{CE} = V_{CES}, V_{GE} = 0 V	-	-	250	uA
I_{GES}	G-E Leakage Current	V_{GE} = V_{GES}, V_{CE} = 0 V	-	-	±400	nA
On Characteristics						
$V_{GE(th)}$	G-E Threshold Voltage	I_C = 40 mA, V_{CE} = V_{GE}	4.8	6.4	8.0	V
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	I_C = 40 A, V_{GE} = 15 V T_C = 25°C	-	2.3	2.9	V
		I_C = 40 A, V_{GE} = 15 V, T_C = 175°C	-	2.7	-	V
Dynamic Characteristics						
C_{ies}	Input Capacitance	V_{CE} = 30 V, V_{GE} = 0 V, f = 1MHz	-	2800	-	pF
C_{oes}	Output Capacitance		-	105	-	pF
C_{res}	Reverse Transfer Capacitance		-	60	-	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{CC} = 600 V, I_C = 40 A, R_G = 23 Ω, V_{GE} = 15 V, Inductive Load, T_C = 25°C	-	45	-	ns
t_r	Rise Time		-	70	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	560	-	ns
t_f	Fall Time		-	15	-	ns
E_{on}	Turn-On Switching Loss		-	4.1	-	mJ
E_{off}	Turn-Off Switching Loss		-	1.0	-	mJ
E_{ts}	Total Switching Loss		-	5.1	-	mJ
$t_{d(on)}$	Turn-On Delay Time	V_{CC} = 600 V, I_C = 40 A, R_G = 23 Ω, V_{GE} = 15 V, Inductive Load, T_C = 175°C	-	43	-	ns
t_r	Rise Time		-	73	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	572	-	ns
t_f	Fall Time		-	58	-	ns
E_{on}	Turn-On Switching Loss		-	6.9	-	mJ
E_{off}	Turn-Off Switching Loss		-	1.9	-	mJ
E_{ts}	Total Switching Loss		-	8.8	-	mJ

Electrical Characteristics of the IGBT (continued)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Q_g	Total Gate Charge	V_{CE} = 600 V, I_C = 40 A, V_{GE} = 15 V	-	226	-	nC
Q_{ge}	Gate to Emitter Charge		-	18	-	nC
Q_{gc}	Gate to Collector Charge		-	155	-	nC

Electrical Characteristics of the DIODE T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_{FM}	Diode Forward Voltage	I_F = 40 A, T_C = 25°C	-	3.6	4.7	V
		I_F = 40 A, T_C = 175°C	-	2.9	-	V
t_{rr}	Diode Reverse Recovery Time	V_R = 600 V, I_F = 40 A, di_F/dt = 200 A/us, T_C = 25°C	-	71	-	ns
I_{rr}	Diode Peak Reverse Recovery Current		-	6.8	-	A
Q_{rr}	Diode Reverse Recovery Charge		-	242	-	nC
E_{rec}	Reverse Recovery Energy	V_R = 600 V, I_F = 40A, di_F/dt = 200 A/us, T_C = 175°C	-	690	-	uJ
t_{rr}	Diode Reverse Recovery Time		-	500	-	ns
I_{rr}	Diode Peak Reverse Recovery Current		-	17	-	A
Q_{rr}	Diode Reverse Recovery Charge		-	4250	-	nC

Typical Performance Characteristics

Figure 1. Typical Output Characteristics

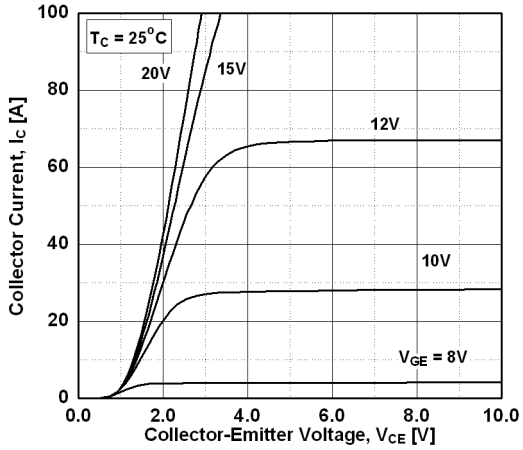


Figure 2. Typical Output Characteristics

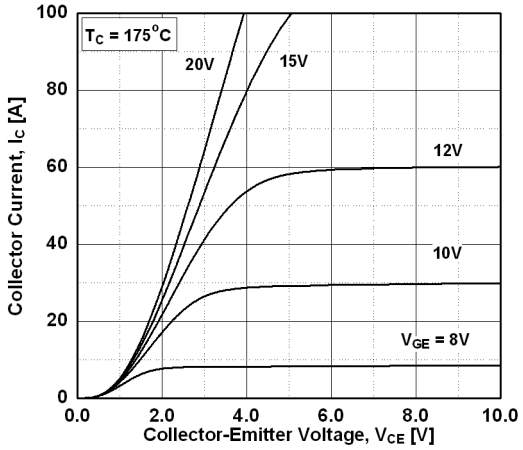


Figure 3. Typical Saturation Voltage Characteristics

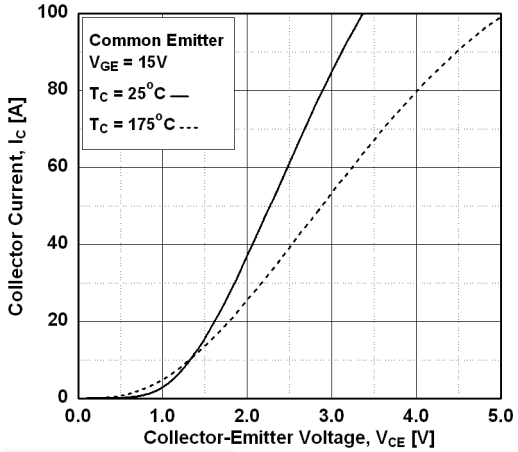


Figure 4. Saturation Voltage vs. Case Temperature at Variant Current Level

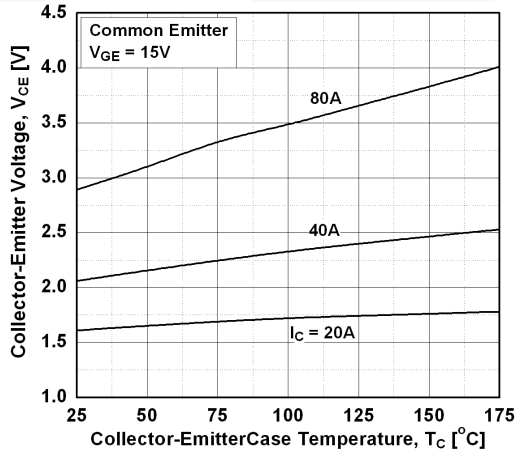


Figure 5. Saturation Voltage vs. V_{GE}

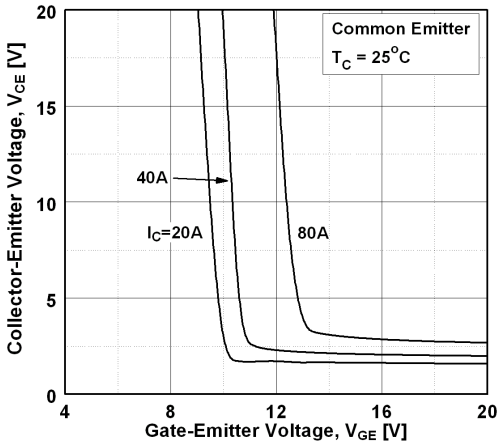
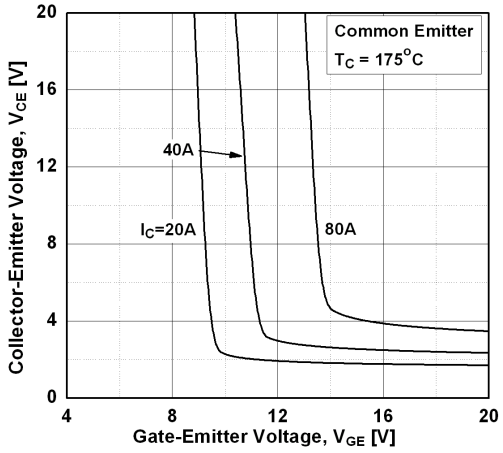


Figure 6. Saturation Voltage vs. V_{GE}



Typical Performance Characteristics

Figure 7. Capacitance Characteristics

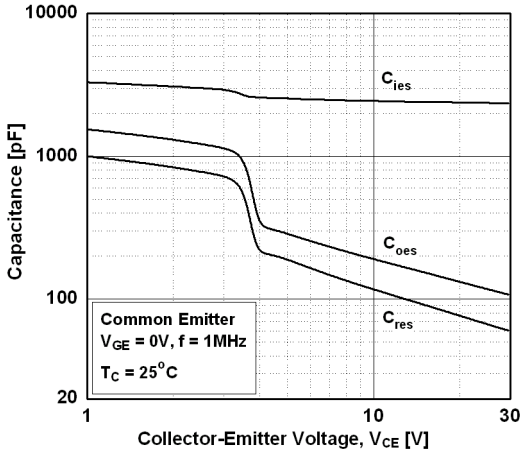


Figure 8. Gate Charge Characteristics

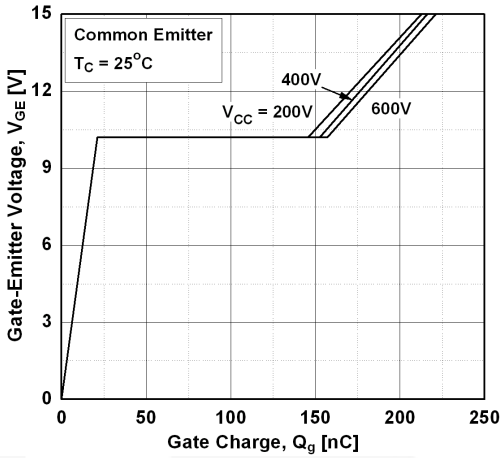


Figure 9. Turn-on Characteristics vs. Gate Resistance

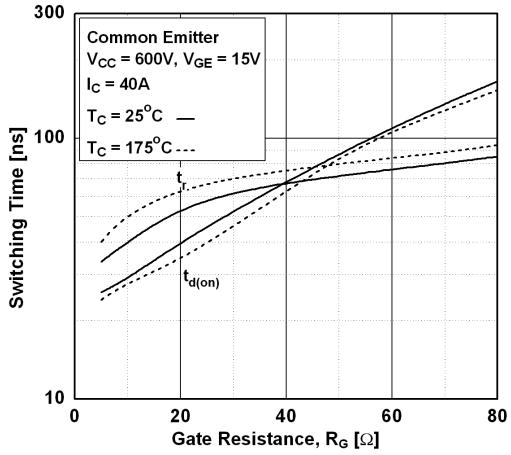


Figure 10. Turn-off Characteristics vs. Gate Resistance

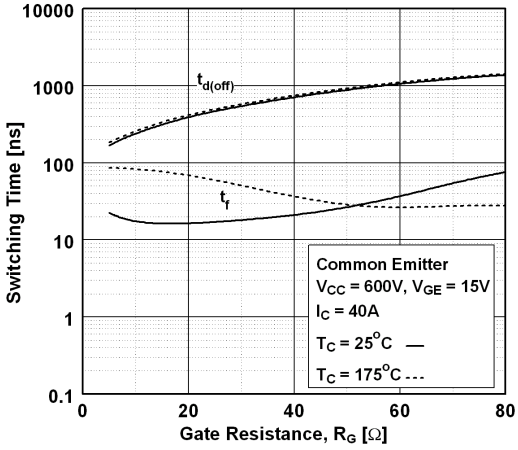


Figure 11. Swithcing Loss vs. Gate Resistance

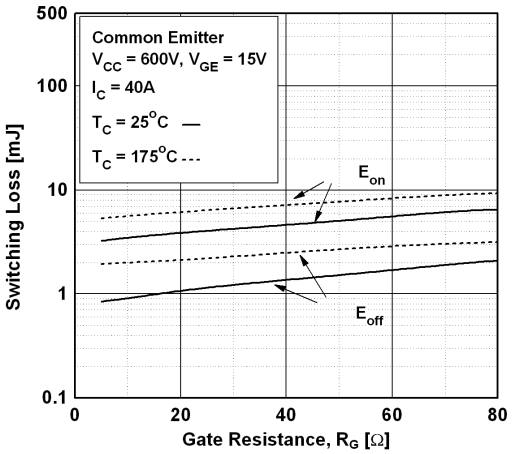
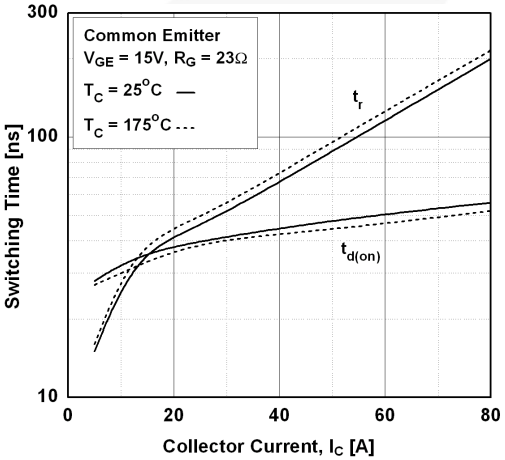


Figure 12. Turn-on Characteristics vs. Collector Current



Typical Performance Characteristics

Figure 13. Turn-off Characteristics vs. Collector Current

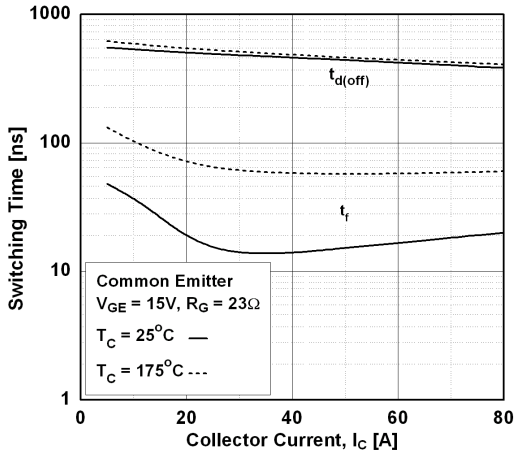


Figure 14. Swithcing Loss vs. Collector Current

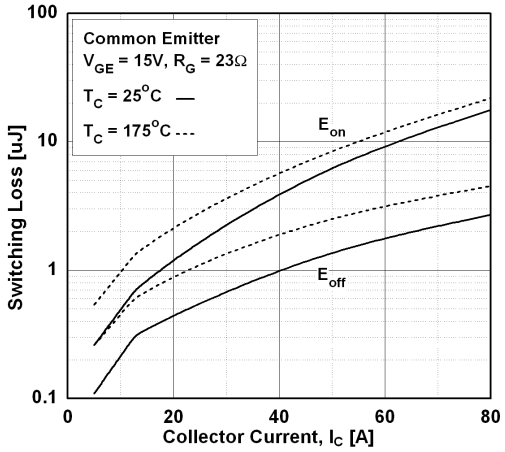


Figure 15. Load Current vs. Frequency

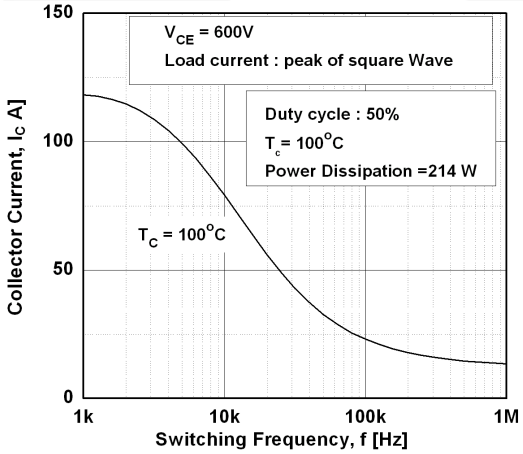


Figure 16. SOA Characteristics

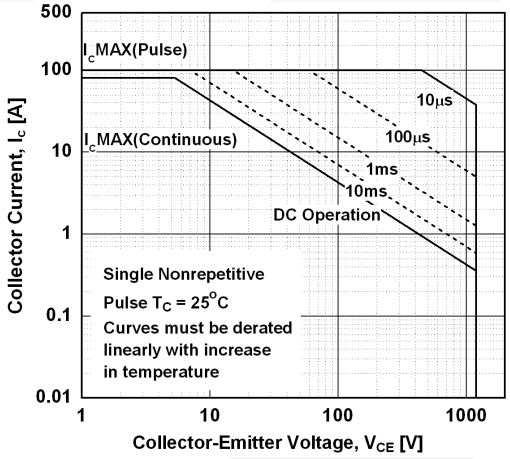


Figure 17. Forward Characteristics

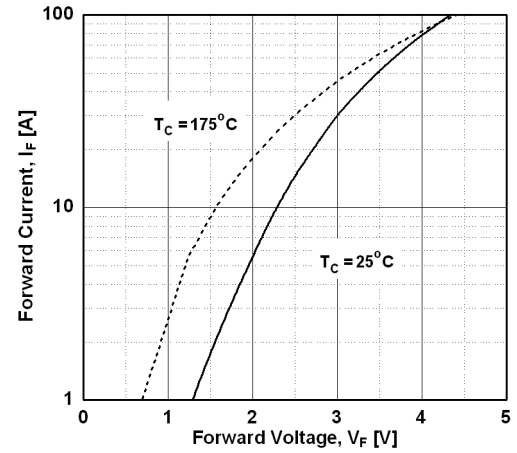
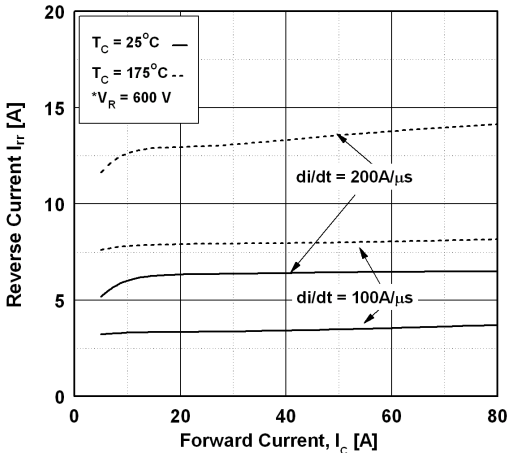


Figure 18. Reverse Recovery Current



Typical Performance Characteristics

Figure 19. Reverse Recovery Time

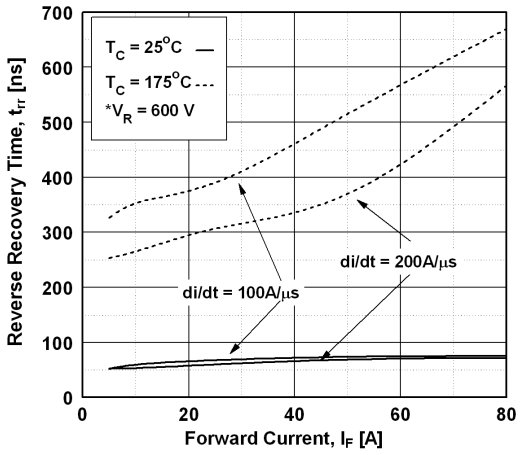


Figure 20. Stored Charge

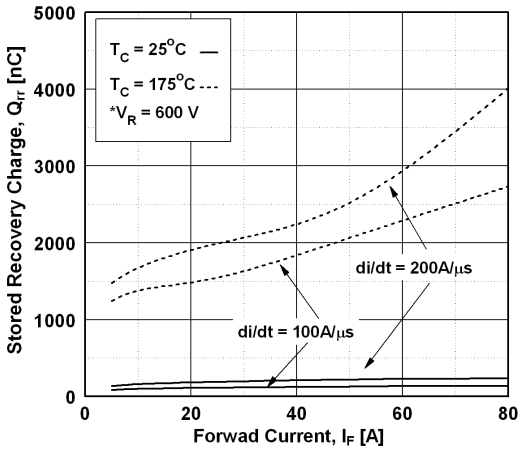


Figure 21. Transient Thermal Impedance of IGBT

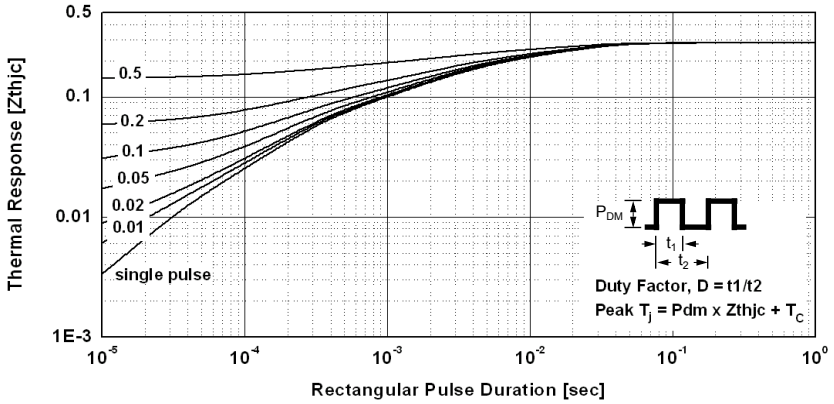


Figure 22. Transient Thermal Impedance of Diode